

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (currently amended): A polishing method, ~~characterized in that comprising:~~ comprising: polishing a surface ~~to be polished~~ of an object ~~to be polished~~ is polished by using a polishing pad ~~while existing an aqueous chemical mechanical polishing solution containing an oxidizing agent between polishing surface of said polishing pad equipped with~~ having a polishing part that ~~contains abrasive~~ is formed by solidifying an aqueous dispersion in which a matrix material and an abrasive are respectively dispersed and contained, while there is present an aqueous chemical mechanical polishing solution containing an oxidizing agent and no abrasive between a polishing surface of said polishing pad having said polishing part and said surface of said object to be polished.

Claim 2 (currently amended): The polishing method according to Claim 4 21, wherein said abrasive is comprised of at least one selected from the group consisting of ceria, silica, alumina, titanium oxide, chromium oxide, manganese dioxide, dimanganese trioxide, iron oxide, zirconium oxide, silicon carbide, boron carbide, diamond and barium carbonate.

Claims 3-4 (canceled)

Claim 5 (currently amended): The polishing method according to Claim 4 2, wherein at least one multivalent metal ion selected from the group consisting of multivalent ions of aluminum, titanium, chromium, manganese, iron, copper, zinc and cerium is further contained in said aqueous chemical mechanical polishing solution.

Claim 6 (original): The polishing method according to Claim 5 wherein an organic acid is contained in said aqueous chemical mechanical polishing solution.

Claim 7 (original): The polishing method according to Claim 6 wherein said surface to be polished of said object to be polished contains at least one element selected from the group consisting of metal elements belonging to the group 3 to 13.

Claim 8 (currently amended): The polishing method according to Claim 7, ~~which is to be~~ used in the manufacture of a semiconductor device.

Claim 9 (currently amended): The polishing method according to Claim 4-2, wherein at least one heterocyclic compound selected from the group consisting of a condensed ring compound composed of a nitrogen-atom-containing penta-heterocyclic compound or a nitrogen-atom-containing hexa-heterocyclic compound and a benzene ring or a naphthalene ring is further contained in said aqueous chemical mechanical polishing solution.

Claim 10 (currently amended): The polishing method according to Claim 9, ~~which is to be~~ used in the manufacture of a semiconductor device.

Claim 11 (currently amended): ~~The A~~ polishing method according to Claim 2, comprising: polishing a surface of an object by using a polishing pad having a polishing part wherein said polishing part that is formed by solidifying an aqueous dispersion containing dispersed composite particles where abrasive is attached to a matrix material, while there is present an aqueous chemical mechanical polishing solution containing an oxidizing agent and

no abrasive between a polishing surface of said polishing pad having said polishing part and said surface of said object.

Claim 12 (canceled)

Claim 13 (currently amended): The polishing method according to Claim 12 34, wherein at least one multivalent metal ion selected from the group consisting of multivalent ions of aluminum, titanium, chromium, manganese, iron, copper, zinc and cerium is further contained in said aqueous chemical mechanical polishing solution.

Claim 14 (original): The polishing method according to Claim 12, wherein an organic acid is contained in said aqueous chemical mechanical polishing solution.

Claim 15 (original): The polishing method according to Claim 14, wherein said surface to be polished of said object to be polished contains at least one element selected from the group consisting of metal elements belonging to the group 3 to 13.

Claim 16 (currently amended): The polishing method according to Claim 15, ~~which is to be~~ used in the manufacture of a semiconductor device.

Claim 17 (currently amended): The polishing method according to Claim 12 34, wherein at least one heterocyclic compound selected from the group consisting of a condensed ring compound composed of a nitrogen-atom-containing penta-heterocyclic compound or a nitrogen-atom-containing hexaheterocyclic compound and a benzene ring or a naphthalene ring is further contained in said aqueous chemical mechanical polishing solution.

Claim 18 (original): The polishing method according to Claim 17 wherein an organic acid is contained in said aqueous chemical mechanical polishing solution.

Claim 19 (original): The polishing method according to Claim 18 wherein said surface to be polished of said object to be polished contains copper.

Claim 20 (currently amended): The polishing method according to Claim 19, ~~which is to be~~ used in the manufacture of a semiconductor device.

Claim 21 (New): The polishing method according to Claim 1, wherein the mean particle diameter of said matrix material is 0.1 to 3 μm and the mean particle diameter of said abrasive is 0.01 to 1 μm .

Claim 22 (New): The polishing method according to Claim 1, wherein said aqueous dispersion is prepared by adding an abrasive or a dispersion containing an abrasive to an emulsion obtained from emulsion polymerization, an emulsion obtained from emulsification using an emulsifying agent, or a suspension obtained from suspension polymerization.

Claim 23 (New): The polishing method according to Claim 22, wherein said abrasive is comprised of at least one selected from the group consisting of ceria, silica, alumina, titanium oxide, chromium oxide, manganese dioxide, dimanganese trioxide, iron oxide, zirconium oxide, silicon carbide, boron carbide, diamond and barium carbonate.

Claim 24 (new): The polishing method according to Claim 23, wherein at least one multivalent metal ion selected from the group consisting of multivalent ions of aluminum, titanium, chromium, manganese, iron, copper, zinc and cerium is further contained in said aqueous chemical mechanical polishing solution.

Claim 25 (new): The polishing method according to Claim 24, wherein an organic acid is contained in said aqueous chemical mechanical polishing solution.

Claim 26 (new): The polishing method according to Claim 25, wherein said surface to be polished of said object to be polished contains at least one element selected from the group consisting of metal elements belonging to the group 3 to 13.

Claim 27 (new): The polishing method according to Claim 26, used in the manufacture of a semiconductor device.

Claim 28 (new): The polishing method according to Claim 23, wherein at least one heterocyclic compound selected from the group consisting of a condensed ring compound composed of a nitrogen-atom-containing penta-heterocyclic compound or a nitrogen-atom-containing hexa-heterocyclic compound and a benzene ring or a naphthalene ring is further contained in said aqueous chemical mechanical polishing solution.

Claim 29 (new): The polishing method according to Claim 28, used in the manufacture of a semiconductor device.

Claim 30 (new): The polishing method according to Claim 22, wherein said aqueous dispersion is prepared by adding an abrasive or a dispersion containing an abrasive to an emulsion obtained from emulsion polymerization.

Claim 31 (new): The polishing method according to Claim 1, wherein said matrix material is comprised of at least one selected from the group consisting of diene-based polymers and styrene-based polymers.

Claim 32 (new): The polishing method according to Claim 11, wherein said matrix material and said abrasive constituting said composite particle are electrostatically attached each other.

Claim 33 (new): The polishing method according to Claim 32, wherein zeta potentials of said matrix material and said abrasive are opposite in sign and potential difference is 5mV or more.

Claim 34 (new): The polishing method according to Claim 11, wherein said abrasive is comprised of at least one selected from the group consisting of ceria, silica, alumina, titanium oxide, chromium oxide, manganese dioxide, dimanganese trioxide, iron oxide, zirconium oxide, silicon carbide, boron carbide, diamond and barium carbonate.